



# BTB06-600SW

Three quadrant triacs

HAOPIN MICROELECTRONICS CO.,LTD.

## Description

Passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commutate the full rated ms current at the maximum rated junction temperature without the aid of a snubber.

Symbol	Simplified outline
Pin	Description
1	Main terminal 1 (T1)
2	Main terminal 2 (T2)
3	gate (G)
TAB	Main terminal 2(T2)

## Applications:

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

## Features

- ◆ Blocking voltage to 600 V
- ◆ On-state RMS current to 6 A

SYMBOL	PARAMETER	Value	Unit
$V_{DRM}$	Repetitive peak off-state voltages	600	V
$I_T$ (RMS)	RMS on-state current (full sine wave)	6	A
$I_{TSM}$	Non-repetitive peak on-state current (full cycle, $T_j$ initial=25°C)	63	A

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{th(j-c)}$	Junction to case(AC)		-	1.8	-	°C/W
$R_{th(j-a)}$	Junction to ambient		-	60	-	°C/W



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Limiting values in accordance with the Maximum system(IEC 134)

SYMBOL	PARAMETER	CONDITIONS			MIN	Value	UNIT	
$V_{DRM}$	Repetitive peak off-state Voltages				-	600	V	
$I_{T(RMS)}$	RMS on-state current	Full sine wave; $T_c \leq 110^\circ\text{C}$			-	6	A	
$I_{TSM}$	Non repetitive surge peak on-state current	full cycle, $T_j$ initial= $25^\circ\text{C}$	F=50Hz	t=20ms	-	60	A	
			F=60Hz	t=16.7ms	-	63	A	
$I^2t$	$I^2t$ Value for fusing	$T_p = 10\text{ms}$			-	21	$\text{A}^2\text{s}$	
DI/dt	Critical rate of rise of on-state current	$IG = 2x I_{GT}, tr \leq 100\text{ns}$ F=120Hz $T_j = 125^\circ\text{C}$			-	50	$\text{A}/\mu\text{s}$	
$I_{GM}$	Peak gate current			$tp = 20\mu\text{s}$	$T_j = 125^\circ\text{C}$	-	4	A
$I_{DRM}$	$V_{DRM} = V_{RRM}$			$T_j = 25^\circ\text{C}$		-	5	$\mu\text{A}$
$I_{RRM}$	$V_{DRM} = V_{RRM}$			$T_j = 125^\circ\text{C}$		-	1	mA
$P_{G(AV)}$	Average gate power			$T_j = 125^\circ\text{C}$		-	1	W
$T_{stg}$	Storage temperature range				-40	150	$^\circ\text{C}$	
$T_j$	Operating junction Temperature range				-40	125	$^\circ\text{C}$	

$T_j = 25^\circ\text{C}$  unless otherwise stated

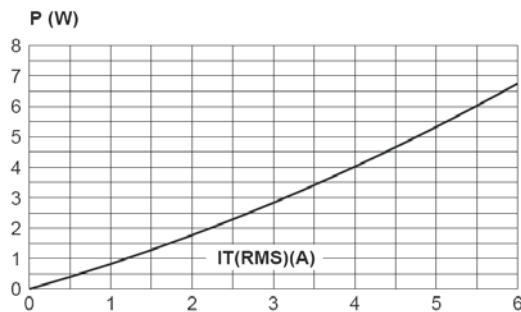
SYMBOL	PARAMETER	CONDITIONS		MIN	TYP	MAX	UNIT
Static characteristics							
$I_{GT1}$		$V_D = 12\text{V}; RL = 30\Omega$	I-II-III	-	-	10	mA
$V_{GT}$			I-II-III			1.3	V
$I_L$	Latching current	$I_G = 1.2 I_{GT}$	I-III II	-	-	25 30	mA mA
$I_H$		$I_T = 100\text{mA}$		-	-	15	mA
$V_{GD}$		$V_D = V_{DRM} R_L = 3.3\text{K}\Omega T_j = 125^\circ\text{C}$	I-II-III	0.2	-	-	V
dV/dt2		$V_D = 67\% V_{DRM}$ gate open; $T_j = 125^\circ\text{C}$		40	-	-	V/us
(Dv/dt)c(2)		$(dV/dt)c = 0.1\text{V}/\mu\text{s}$ $T_j = 125^\circ\text{C}$ $(dV/dt)c = 10\text{V}/\mu\text{s}$ $T_j = 125^\circ\text{C}$		3.5 2.4	-	-	A/ms

## Dynamic Characteristics

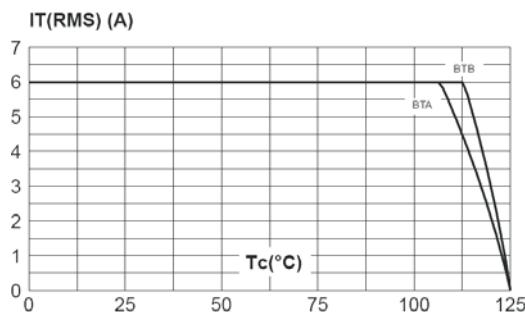
$V_T(2)$	$I_{TM} = 5.5\text{A}$ $tp = 380\mu\text{s}$	$T_j = 25^\circ\text{C}$	-	-	1.55	V
$V_{to}$ $R_d$	Threshold voltage Dynamic resistance	$T_j = 125^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	0.85 60	$\text{V}/\text{m}\Omega$

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**Description**

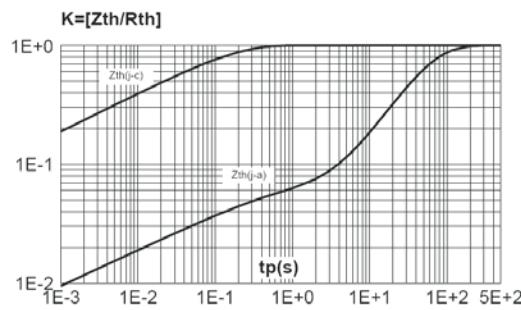
**Fig. 1:** Maximum power dissipation versus RMS on-state current (full cycle).



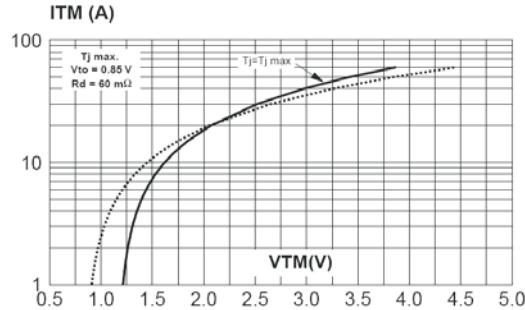
**Fig. 2:** RMS on-state current versus case temperature (full cycle).



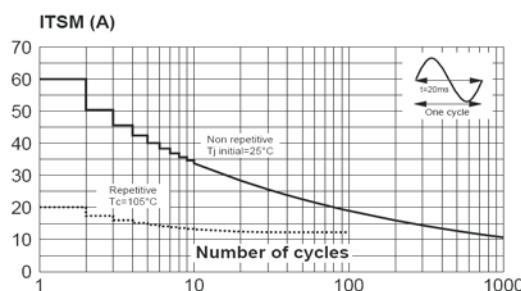
**Fig. 3:** Relative variation of thermal impedance versus pulse duration.



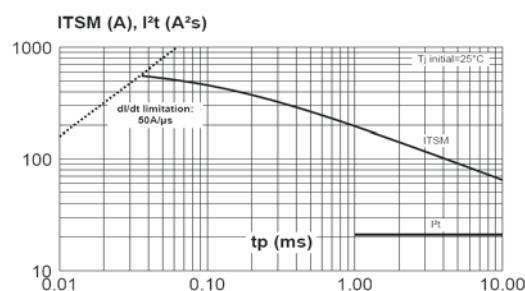
**Fig. 4:** On-state characteristics (maximum values).



**Fig. 5:** Surge peak on-state current versus number of cycles.

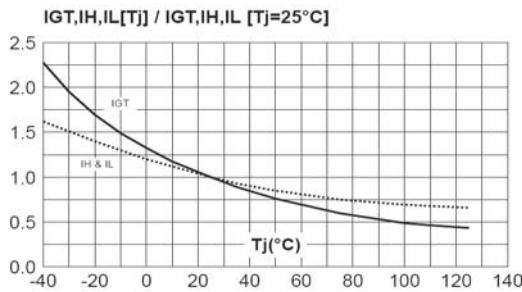


**Fig. 6:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$ .

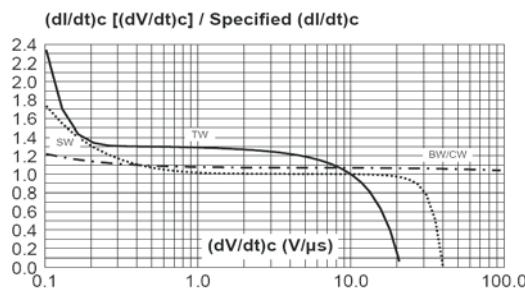


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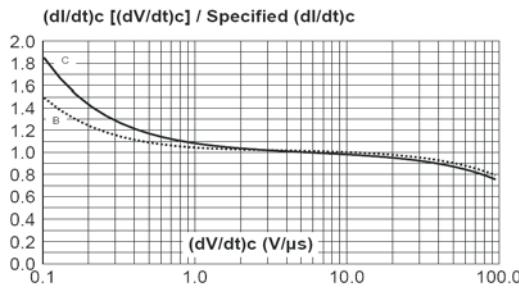
**Fig. 7:** Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).



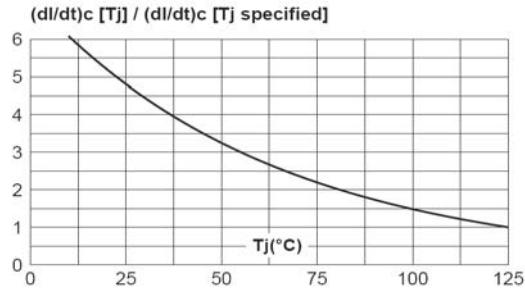
**Fig. 8-1:** Relative variation of critical rate of decrease of main current versus  $(dV/dt)c$  (typical values). Snubberless & Logic Level Types



**Fig. 8-2:** Relative variation of critical rate of decrease of main current versus  $(dV/dt)c$  (typical values). Standard Types

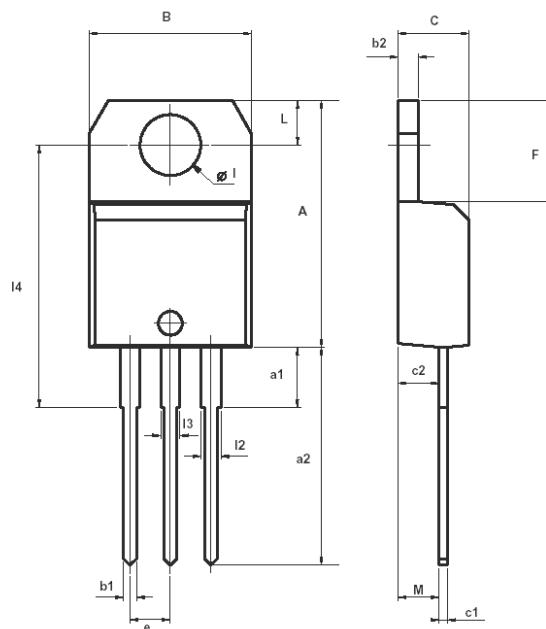


**Fig. 9:** Relative variation of critical rate of decrease of main current versus junction temperature.



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**MECHANICAL DATA**

Dimensions in mm  
Net Mass: 2 g



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
I	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
I3	1.14		1.70	0.044		0.066
M		2.60			0.102	